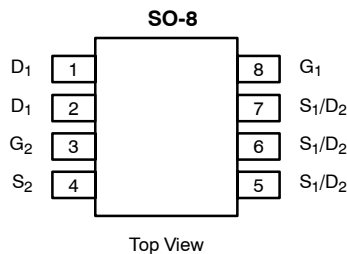




Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
	V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
Channel-1	30	0.021 @ V _{GS} = 10 V	7.0
		0.0325 @ V _{GS} = 4.5 V	5.6
Channel-2		0.020 @ V _{GS} = 10 V	7.4
		0.0265 @ V _{GS} = 4.5 V	6.4

SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.50 V @ 1.0 A	2.0



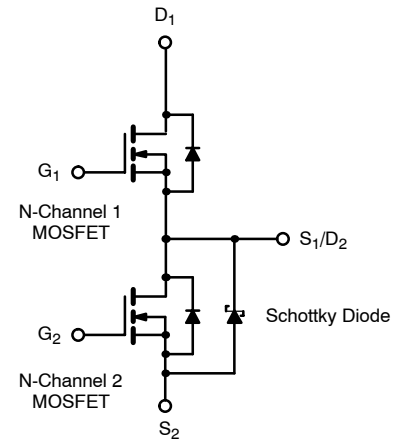
Ordering Information: Si4814DY
Si4814DY-T1 (with Tape and Reel)

FEATURES

- LITTLE FOOT® Plus Integrated Schottky
- Alternative Pinning for Additional Layout Options
- 100% R_g Tested

APPLICATIONS

- DC/DC Converters
– Notebook



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		10 secs	Steady State	10 secs	Steady State		
Drain-Source Voltage	V _{DS}	30				V	
Gate-Source Voltage	V _{GS}	20					
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	7.0	5.5	7.4	5.7	A
		T _A = 70 °C	5.6	4.3	6	4.5	
Pulsed Drain Current	I _{DM}	40		40		A	
Continuous Source Current (Diode Conduction) ^a	I _S	1.7	1.0	1.8	0.95		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	1.9	1.1	2.0	1.16	W
		T _A = 70 °C	1.2	0.71	1.3	0.74	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150				°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		Typ	Max	Typ	Max		
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 sec	52	65	47	60	°C/W
		Steady-State	90	112	85	107	
Maximum Junction-to-Foot (Drain)	R _{thJF}	30	38	28	35		

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition		Min	Typ ^a	Max	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	0.8			V
			Ch-2	0.8			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V	Ch-1			100	nA
			Ch-2			100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			1	μA
			Ch-2			100	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1			15	
			Ch-2			2000	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	Ch-1	20			A
			Ch-2	20			
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 7.0 A	Ch-1		0.0175	0.021	Ω
		V _{GS} = 10 V, I _D = 7.4 A	Ch-2		0.0165	0.020	
		V _{GS} = 4.5 V, I _D = 5.6 A	Ch-1		0.027	0.0325	
		V _{GS} = 4.5 V, I _D = 6.4 A	Ch-2		0.022	0.0265	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.0 A	Ch-1		17		S
		V _{DS} = 15 V, I _D = 7.4 A	Ch-2		20		
Diode Forward Voltage ^b	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	Ch-1		0.7	1.1	V
		I _S = 1 A, V _{GS} = 0 V	Ch-2		0.47	0.5	
Dynamic^a							
Total Gate Charge	Q _g	Channel-1 V _{DS} = 15 V, V _{GS} = 5 V, I _D = 7.0 A Channel-2 V _{DS} = 15 V, V _{GS} = 5 V, I _D = -7.4 A	Ch-1		6.5	10	nC
			Ch-2		9.7	15	
Gate-Source Charge	Q _{gs}		Ch-1		1.5		nC
Gate-Drain Charge	Q _{gd}		Ch-2		2.6		
Gate Resistance	R _g		Ch-1	0.5	1.6	2.6	Ω
			Ch-2	0.5	1.8	3.1	
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω Channel-2 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω	Ch-1		12	20	ns
Rise Time	t _r		Ch-2		13	20	
		Ch-1		13	20		
Turn-Off Delay Time	t _{d(off)}	Ch-1		22	35		
		Ch-2		29	45		
Fall Time	t _f	Ch-1		8	15		
		Ch-2		12	20		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.3 A, di/dt = 100 A/μs	Ch-1		50	80	
		I _F = 2.2 A, di/dt = 100 μA/μs	Ch-2		46	80	

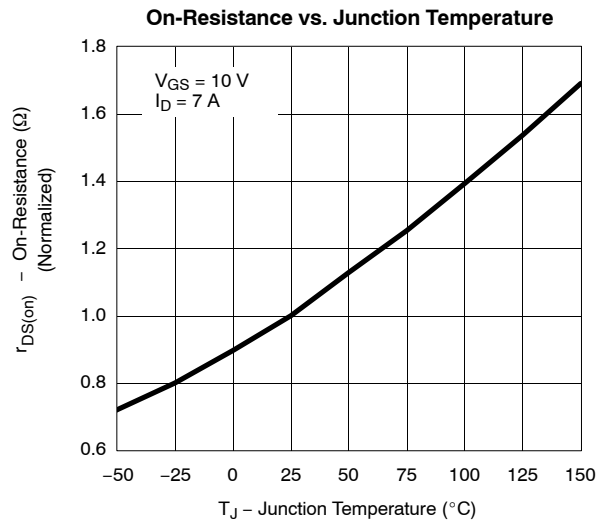
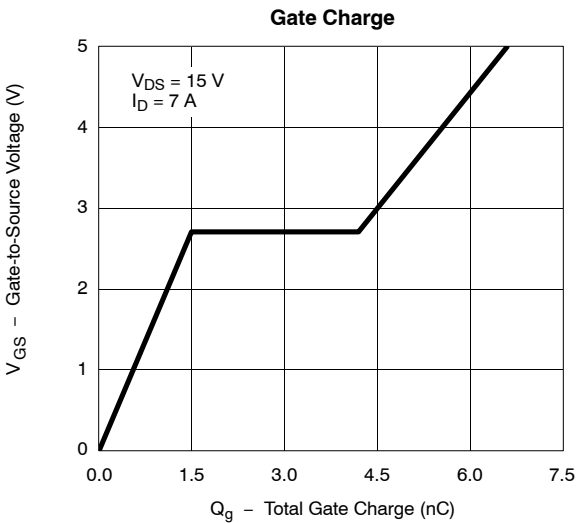
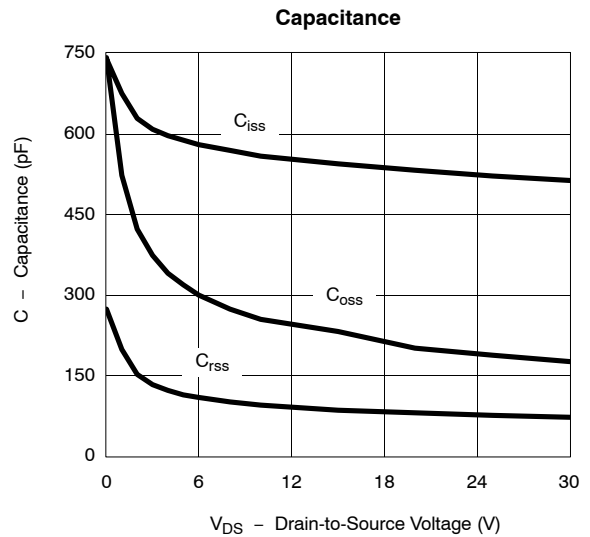
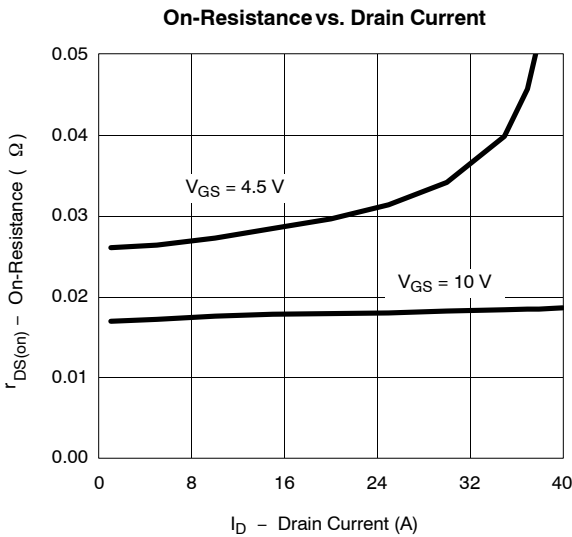
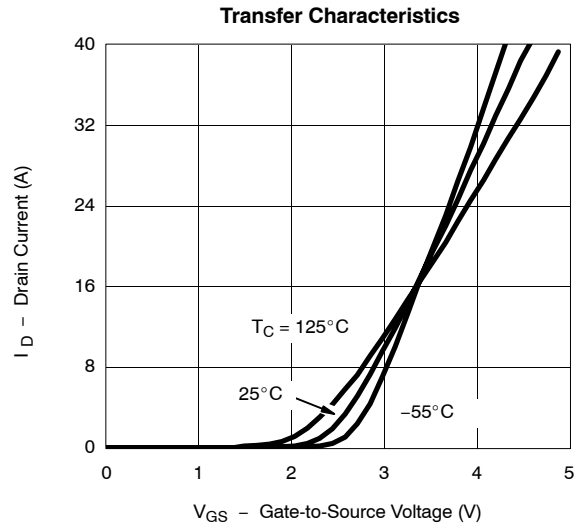
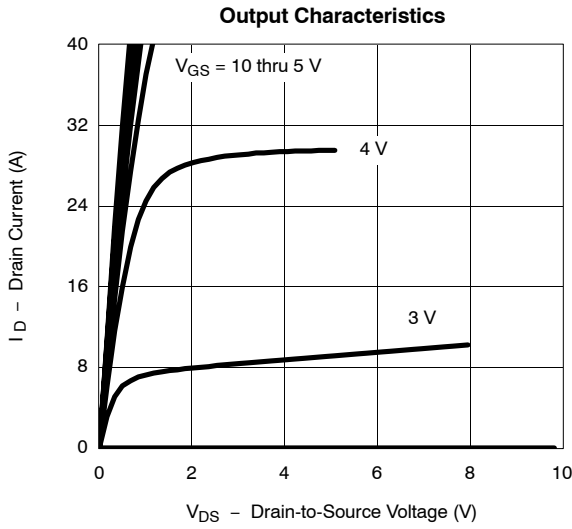
Notes

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

SCHOTTKY SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Forward Voltage Drop	V _F	I _F = 1.0 A			0.47	0.50	V
		I _F = 1.0 A, T _J = 125 °C			0.36	0.42	
Maximum Reverse Leakage Current	I _{rm}	V _r = 30 V			0.004	0.100	mA
		V _r = 30 V, T _J = 100 °C			0.7	10	
		V _r = -30 V, T _J = 125 °C			3.0	20	
Junction Capacitance	C _T	V _r = 10 V			50		pF



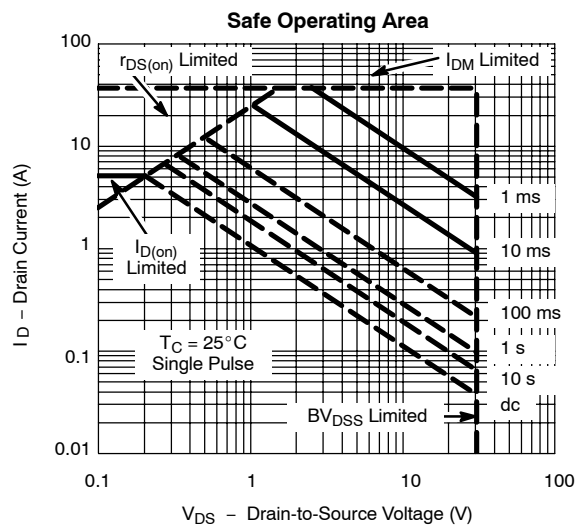
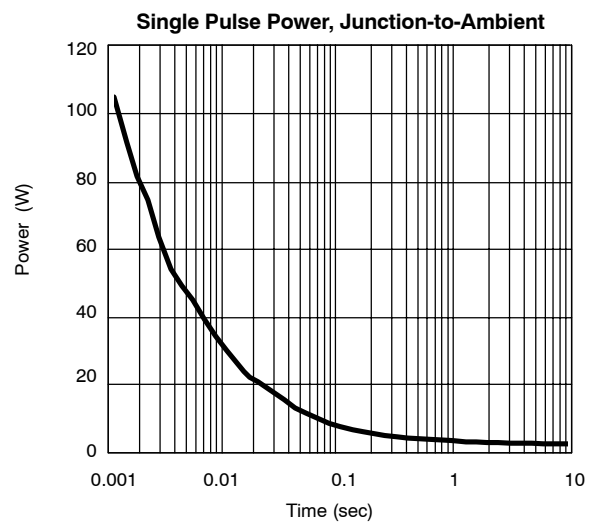
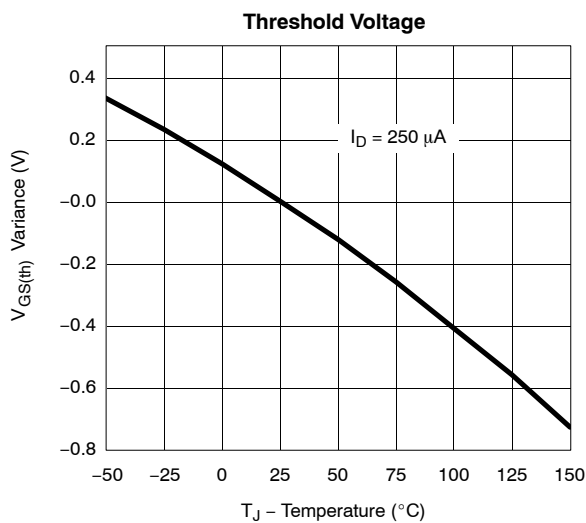
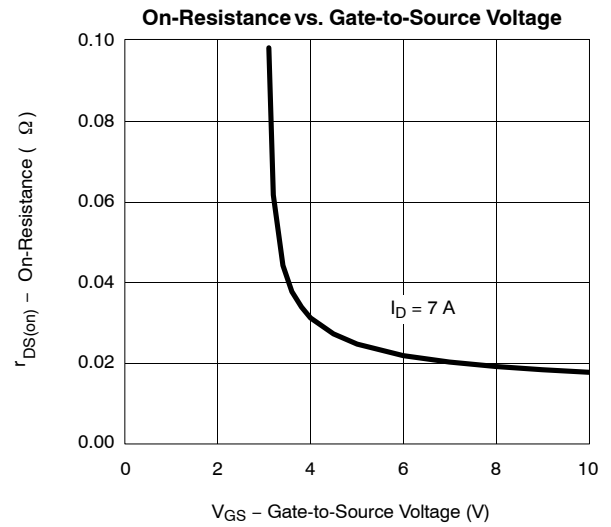
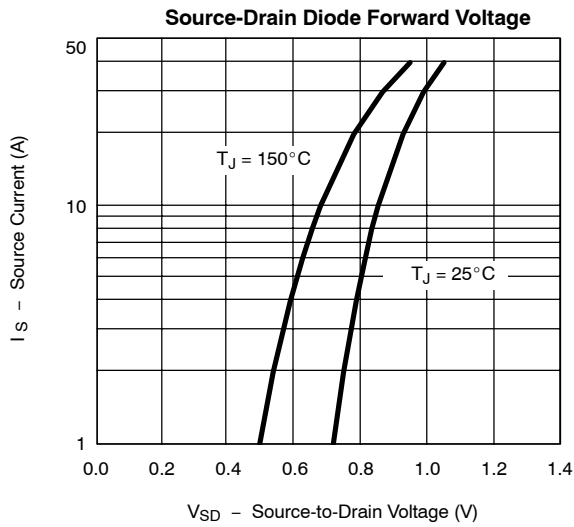
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) CHANNEL-1



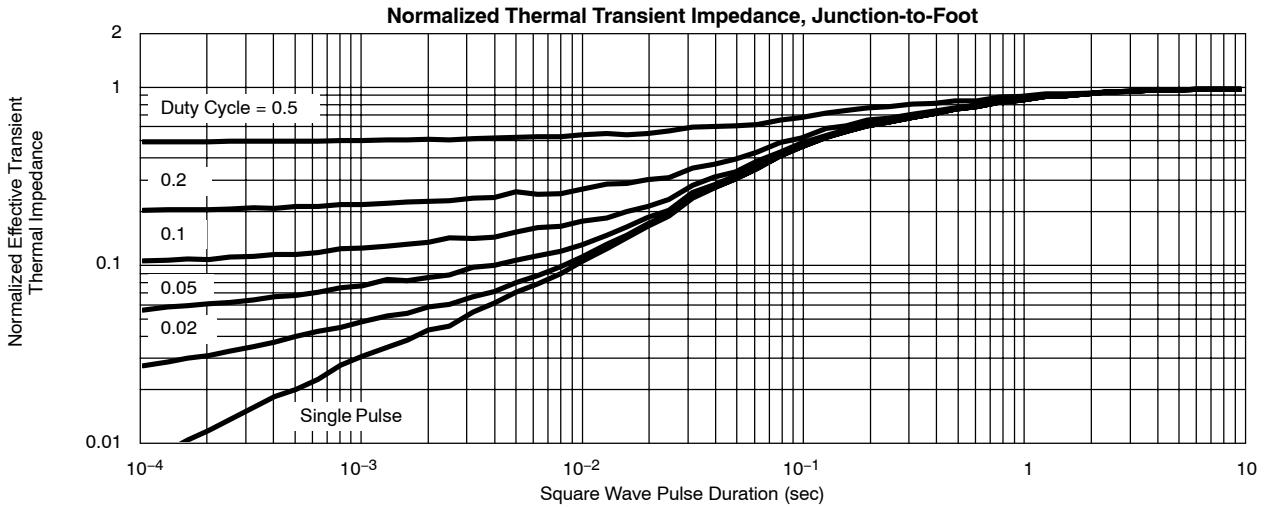
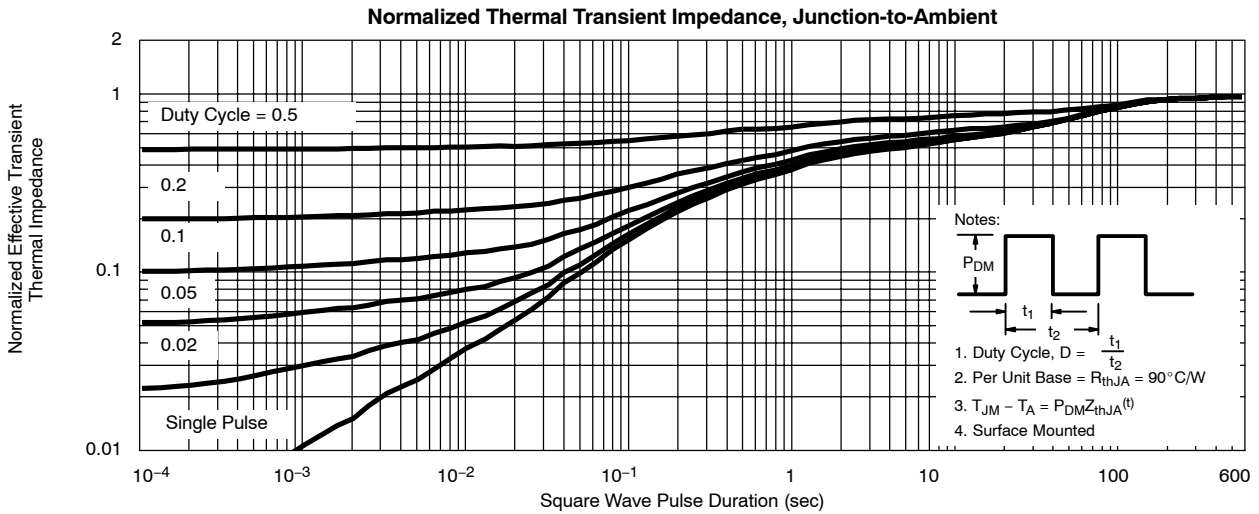


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

CHANNEL-1

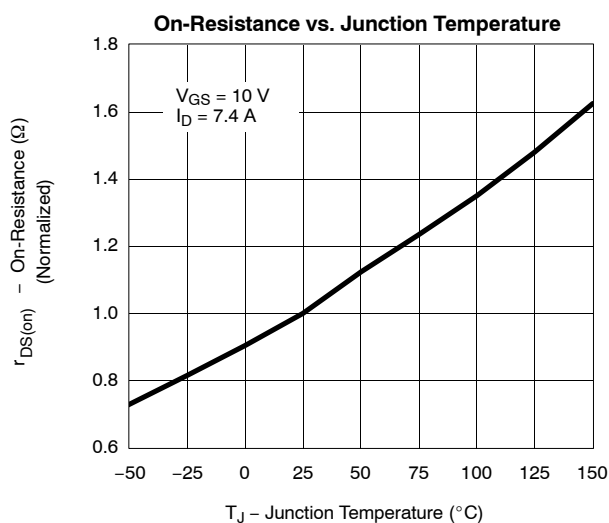
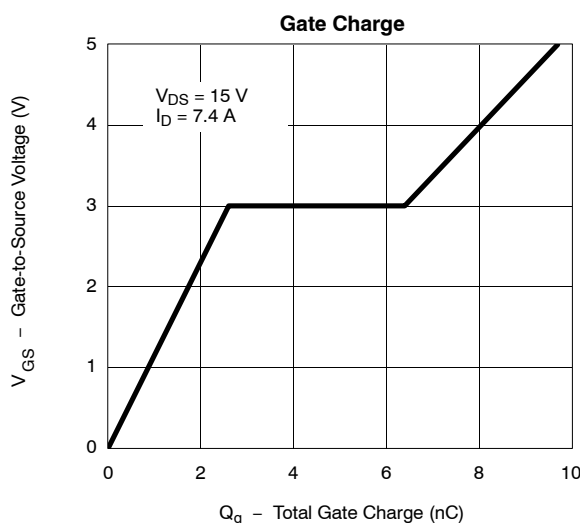
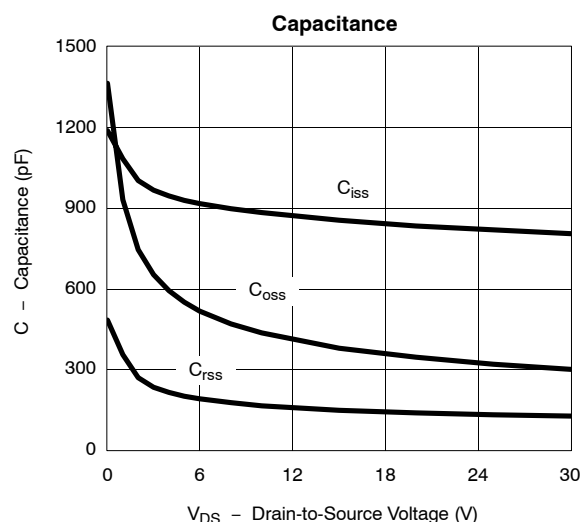
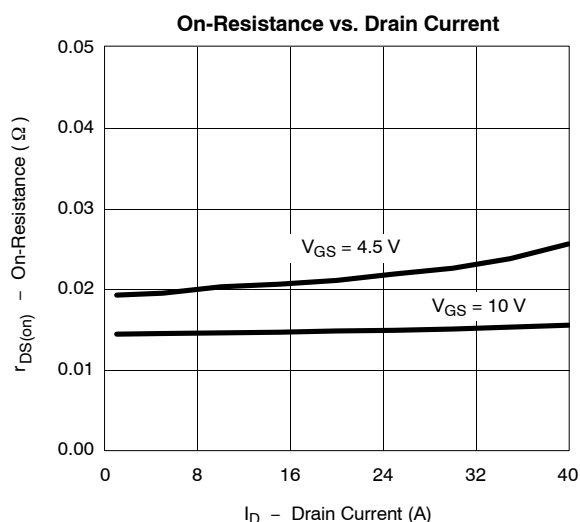
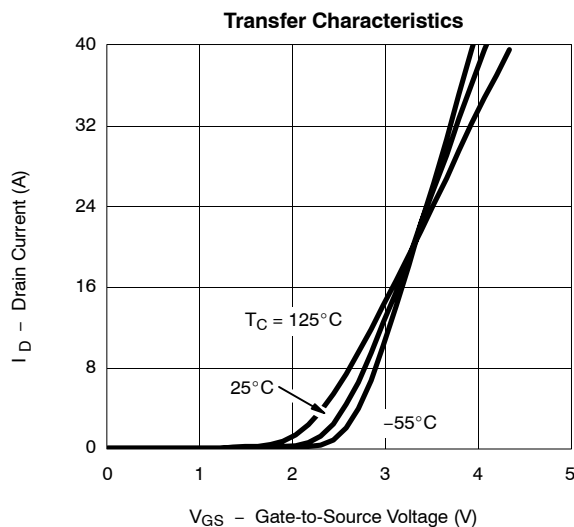
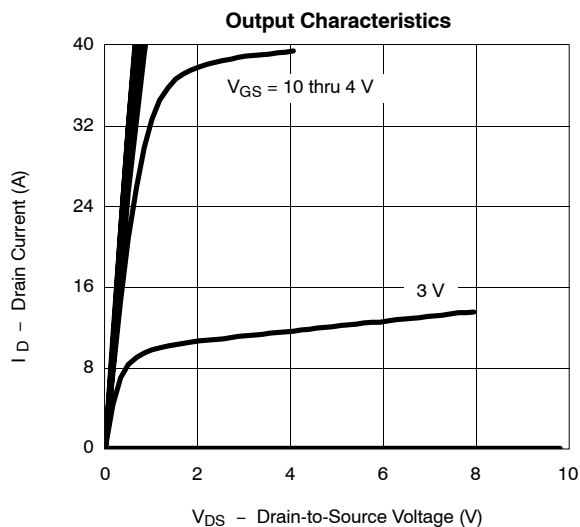


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) CHANNEL-1

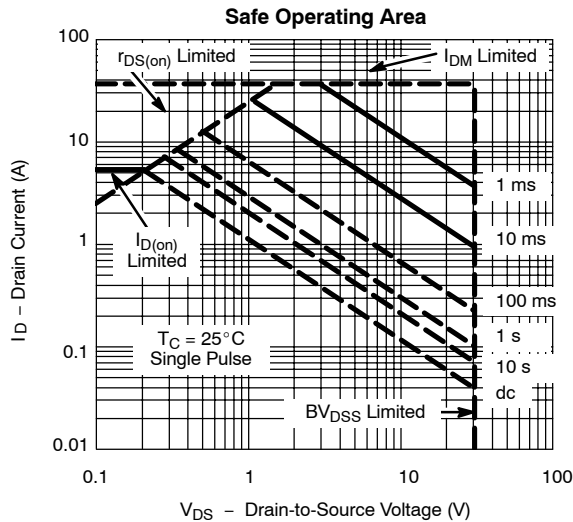
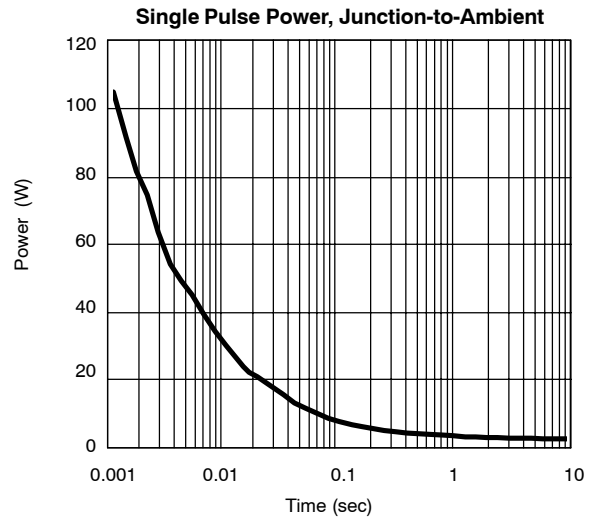
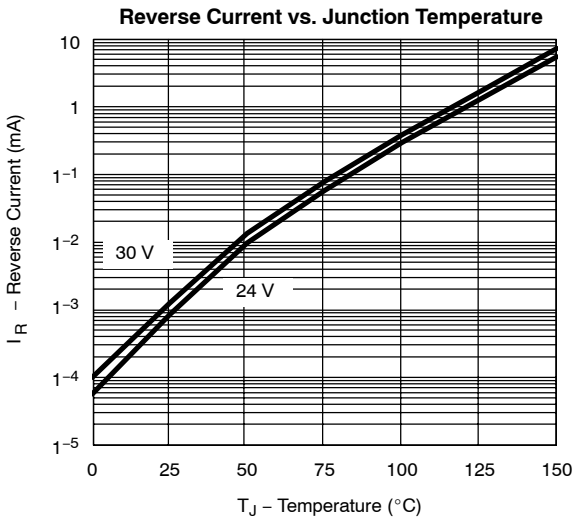
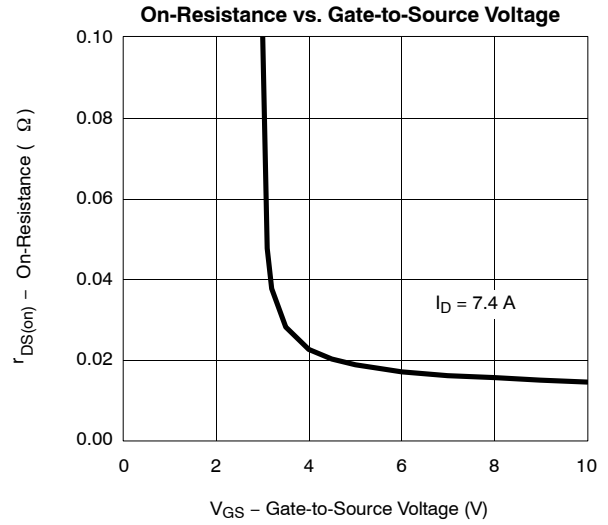
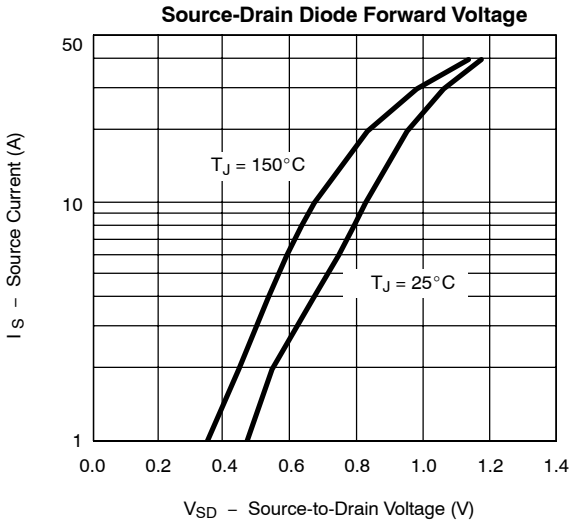


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CHANNEL-2

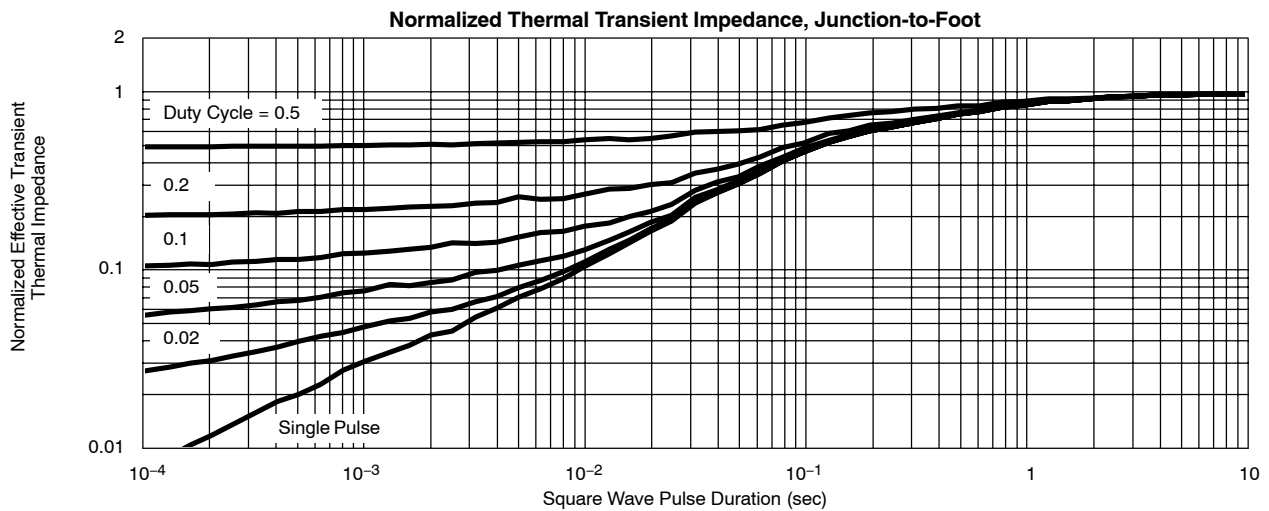
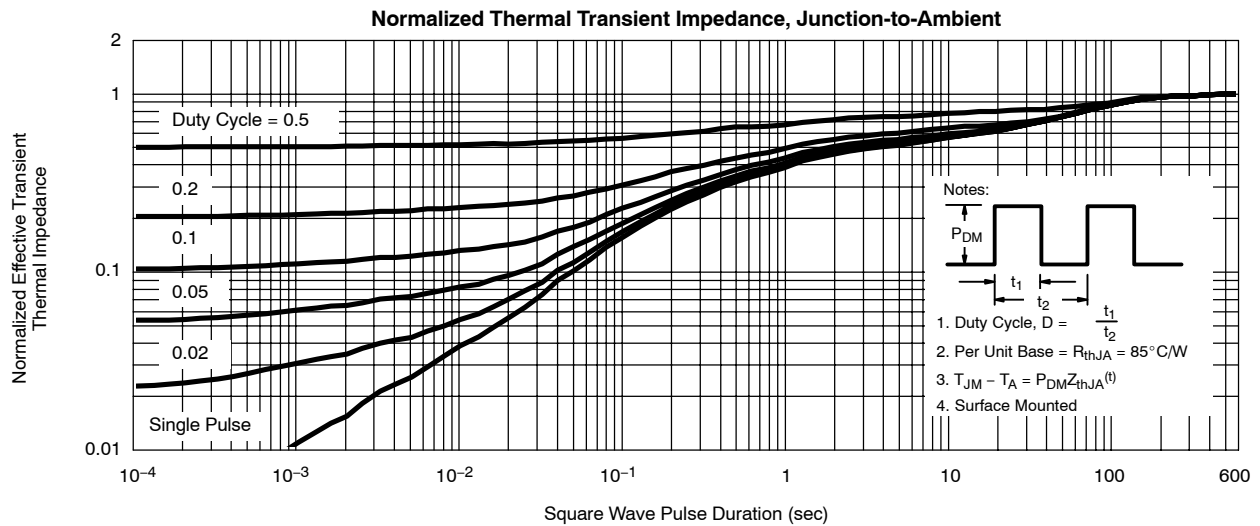


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) CHANNEL-2



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

CHANNEL-2





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